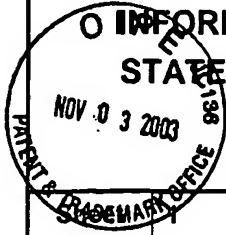


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**INFORMATION DISCLOSURE  
STATEMENT BY APPLICANT**



Application Number **10/038,745**  
 Filing Date **January 2, 2002**  
 First Named Inventor **Robert Jackson**  
 Group Art Unit **1754**  
 Examiner Name **Ngoc Nguyen**  
 Attorney Docket Number **FOC1100-1**

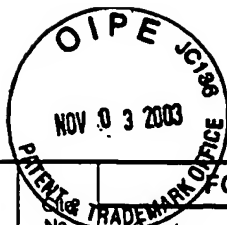
OF 1

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*Ngoc - yen Nguyen*

*6/17/06*



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I	B2	JP08017804			01/19/96	Sony Corp.	
yn	B3	EP 0 819 780		A2	01/21/98	Applied Materials, Inc.	
Examiner Signature	Ngaz-yen Nguyen				Date Considered	6/17/06	

FORM PTO 1449 US Department of Commerce Patent and Trademark Office NOV 03 2003		Application Number	10/038,745
		Filing Date	January 2, 2002
		First Named Inventor	Robert Jackson
		Group Art Unit	1754
		Examiner Name	Ngoc Nguyen
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	C3	Astron, "Reactive Gas Generators," MKS Instruments, Inc., 4 pages.	
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	C5	Kranefuss, "Etching System," IBM Technical Disclosure Bulletin, Vol. 9, No. 8, pg. 2956.	January 1977
	C6	"Anisotropic and Selective Etching of Tungsten Silicide-Tungsten-Tungsten Silicide Composite Stack," IBM Technical Disclosure Bulletin, Vol. 29, No. 3., pg. 1151.	August 1986
	C7	Bergendahl, et al., "Positive Photoresist for Permeation Etching," IBM Technical Disclosure Bulletin, Vol. 23, No. 10, pg. 4446.	March 1981
	C8	Flamm et al., "Reaction of Fluorine Atoms with SiO <sub>2</sub> ," J. Appl. Phys., 50 (10), pages 6211-3,	October 1980
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Ngoc - Yen Nguyen

6/17/06



PTO/SB/08A (04-03)

**INFORMATION DISCLOSURE  
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Attorney Docket Number	FOC1100-1

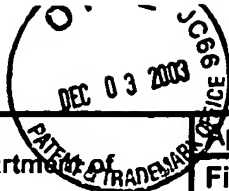
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**U.S. PATENT DOCUMENTS**

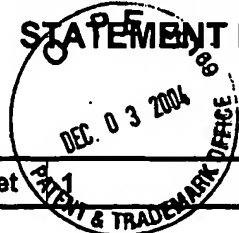
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yn	B6	JP 3183125			09/08/91	Semiconductor Energy Lab Co. Ltd.	
Examiner Signature		Ngoc - yun Nguyen			Date Considered	6/17/06	



<b>FORM PTO 1449 US D partment of Commerce Patent and Trademark Office</b>				<b>Application Number</b>	10/038,745
				<b>Filing Date</b>	January 2, 2002
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				<b>Group Art Unit</b>	1754
				<b>Examiner Name</b>	Ngoc Nguyen
<b>Sheet</b>	2	<b>of</b>	2	<b>Atty Docket Number</b>	FOC1100-1
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yn	C15	Working Agreement between Syngen Enterprises Ltd. and Fluorogas Ltd., Client I: Applied Materials, Exhibit P-1.			October 1998
yn	C16	Working Agreement between Syngen Enterprises Ltd. and Fluorogas Ltd., Client II: Novellus, Exhibit P-2.			October 1998
<b>Examiner Signature</b>	Ngoc Nguyen			<b>Date Considered</b>	6/17/06

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Application Number	10/038,745
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Examiner Name	Nguyen, Ngoc Yen M
Attorney Docket Number	FOC1100-1

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NN	B8	WO	99/28538	A	06/10/1999	Fluorogas Limited	

 Examiner  
Signature

/Ngoc Yen Nguyen/ (06/17/2006)

 Date  
Considered